





	INPUT POWER - DESIGN CHECKLIST									
PIN NAN	ΛE	REQUIREMENT	COMPONENT	MIN	ТҮР	MAX	DESCRIPTION	COMMENTS AND RELEVANT EQUATIONS		
							Input source to the charger			
		Recommended	Q1		-		Back-to-back input protection P-	Used to isolate the battery and adapter. This blocks reverse current from the battery back the input. If Q1 not included, use diode to block reverse current		
ADAPTER+			Q2		-		Channel MOSFETs	Used to isolate the battery and adapter. This also limits inrush current to the system by providing limited dI/dt when connecting the adapter to the system by controlling the FET turn-on time		
/ ADAPTER-	-	Deserves and ad	R1/R2		2Ω		Input hot-plug snubber	Used to dampen ringing due to input inrush current		
		Recommended	C2/C32		2.2 uF		circuit			
		Recommended	R3		100 kΩ					
		neconnenaca	C4		0.1 uF		Input MOSEETs turn-on/turn-off delay			
		Ontional	R21					Additional turn-on delay for Q2 to further limit dI/dt and limit inrush current		
		optional	C34							
							Differential input current sensing			
	1-2	Required	R9 (R <sub>AC</sub> )		10 mΩ		Input current sensing resistor	$I_{DMM} = \frac{V_{ACMT}}{20 \times R_{AC}}$		
ACP-ACN		Recommended	C7		0.1 uF		Differential mode noise filtering	Filter differential-mode voltage to avoid amplification of high frequency signals, for more accurate current sensing		
		Recommended	C5		0.1 uF		Common mode noise filtering	Filter common-mode voltage to avoid amplificaiton of high frequency signals, for more accurate		
		Optional	C9		0.1 uF		Common mode noise intering	current sensing		
		Optional	R10							
							P-Channel MOSFET input protection gate driver			
/ACDRV	3	Recommended	R24		1 kΩ		Input MOSFETs gate drive strength limiting resistor	Increase turn-on time to limit inrush current		
		Optional	D9				Input MOSFETs gate-source Zener clamp	Clamp Vgs under MOSFET abs. max. Vgs to protect MOSFET		
							IC power positive supply			
VCC	24	Required	R22		10 Ω		VCC inrush current limiting			
		Required	C12		1.0 uF		VCC decoupling capacitor			





PIN NAME		REQUIREMENT	COMPONENT	MIN	ТҮР	MAX	DESCRIPTION	COMMENTS AND RELEVANT EQUATIONS
	-						System output either from input source or battery	
SYSTEM+		Required	C10/C11		10 uF		High frequency converter input capacitor(s)	
		Required	C28/C29		10 uF		System output noise filtering capacitor(s)	
		Recommended	C14		10 nF		High frequency noise decoupling capacitor	
	23						P-Channel BATFET power path gate driver	
		Recommended	Q5		-		External P-Channel BATFET for power path	If power path is not needed, remove Q5 and float BATDRV as shown in BQ24610 Simplified Non PowerPath
/BATDRV		Recommended	R27		1 kΩ		Input MOSFETs gate drive strength limiting resistor	Increase turn-on time to limit shoot-through current
		Recommended	R20		100 kΩ		External BATFET turn-on/turn-off	
			C24		0.1 uF		delay	
BATTERY PACK+ /	-						Battery or battery pack connection to the charger	
BATTERY PACK-		Required	C20/C23/C25/C27		*uF		Converter ouput filtering capacitor(s)	$f_o = \frac{1}{2 \cdot \pi \cdot \sqrt{L_{out} \cdot C_{out}}}$ Recommended: 12 kHz < fo < 17 kHz
							Battery regulation voltage feedback	
		Required	R25		*kΩ		Resistor divider feedback for battery	$H_{1} = (A_{1}, R_{25}, \dots, A_{11})$
VFB	12		R28		*kΩ		voltage regulation setting	$\frac{v_{BATREG} = (1 + \frac{1}{R_{28}}) \times 2.1 V}{v_{RECHG} = (1 + \frac{1}{R_{28}}) \times 2.05 V} \qquad \frac{v_{BATLOWV} = (1 + \frac{1}{R_{28}}) \times 1.55 V}{v_{BATLOWV} = (1 + \frac{1}{R_{28}}) \times 1.55 V}$
		Optional	C26		100 nF		High frequency noise decoupling capacitor	
		Optional	C22		22pF			
		Optional	C31		DNP			

	OUTPUT POWER - DESIGN CHECKLIST										
							0.000	SYSTEM+			
				Ţ,	514	₫	= C10/C11	$\downarrow \qquad \downarrow \qquad \downarrow \qquad \downarrow \qquad \qquad \downarrow \qquad \qquad \downarrow \qquad \qquad \downarrow \qquad \qquad \qquad \downarrow \qquad \qquad \qquad \qquad \qquad \downarrow \qquad \qquad$			
		/BAT HI R LC	VCC DRV PH RT14 attst C15 GND C15 SRP				R27 R20 =	BATTERY PACK + C20/C23/C25/C27 BATTERY PACK - C21 ↓ C21 ↓ C22 R25 C26			
								↓			
							Differential charge current sensing				
	12	Required	R18 (R <sub>SR</sub> )		10 mΩ		Charge current sensing resistor	$I_{CHARGE} = \frac{V_{ISET 1}}{20 \times R_{SR}}$			
SRP-SRN	14	Recommended	C19		0.1 uF		Differential mode noise filtering	Filter differential-mode voltage to avoid amplification of high frequency signals, for more accurate current sensing			
		Recommended	C17		0.1 uF		Common mode noise filtering	Filter common-mode voltage to avoid amplificaiton of high frequency signals, for more accurate			
		Optional	R19		DNP						
			045		4.0.5		Internal LDO output Internal LDO output stabilizing				
REGN	18	Required	C15		1.0 uF		capacitor	Schottky diodes reduce the risk associated with charge supplied back to the gate driver supply from the			
		Required	D1				Bootstrap capacitor refresh and blocking Schottky diode	bootstrap capacitor and minimize leakage current. Fast reverse recovery minimizes losses			
							Converter Low-Side N-Channel				
	19						MOSFET gate driver				
LODIN	15	Required	Q4		-		Converter synchronous Low-Side N- Channel MOSFET				
							PH node				
		Required	L1		*uH		Converter output filtering inductor	$f_o = \frac{1}{2 \cdot \pi \cdot \sqrt{L_{out} \cdot C_{out}}}$ Recommended: 12 kHz < fo < 17 kHz			
	20	Required	C16		0.1 uF		Converter bootstrap capacitor for High-Side N-Channel MOSFET gate driver				
FIGDISI	22	Recommended	R14		10 Ω		Bootstrap capacitor discharge current limiting resistor	Limits peak current through bootstrap diode, and also reduces switch node ringing by slowing down turn-on of HSFET			
		Recommended	R <sub>SNUB</sub>		DNP		Switching converter snubber circuit	Reduce switch node ringing on HSFET turn-on. Recommended to include footprint for evaluation, in case			
			L <sub>SNUB</sub>	-	UNP	-	Fast recovery and asynchronous	Reduce reverse recovery loss as compared to internal body diode of LSFET, which helps reduce switch node			
		Recommended	D2				rectifier Schottky diode	ringing, as well as increase efficiency due to lower forward voltage drop of schottky as compared to forward voltage drop of internal body diode			
							Converter High-Side N-Channel MOSFET gate driver				
		Required	Q3		-		Converter active High-Side N-Channel MOSFET				
HIDRV	21	Recommended	R17				Converter active High-Side MOSFET gate drive strength limiting resistor	Increase turn-on time of HSFET to reduce ringing at PH node. Also increases turn-off time and reduces efficiency			
		Optional	D10				Diode for fast High-Side MOSFET turn- off	Adding gate resistor limits turn-on and turn-off of HSFET resulting in lower efficiency. Diode allows fatser turn- off and slower turn-on, reducing ringing on HSFET turn-on, and also reducing effects on efficiency by turning off faster.			
GND	17						IC Ground return				

## BQ24610 - Hardware Programmed Input Design



	HARDWARE PROGRAMMED INPUT - DESIGN CHECKLIST											
PIN		REQUIREMENT	COMPONENT	MIN	TYP N	IAX DESCRIPTION	COMMENTS AND RELEVANT EQUATIONS					
						Battery thermistor temperature qualification window setting resistor network						
		Required	R4		*Ω	Resistor network to set window for						
		Required	R5		*Ω	thermistor temperature-based battery charging profile						
TS	6	Recommended	RTH		*Ω	External battey thermistor						
		Recommended	R8		100 Ω	Current limiting resistor for TS pin transient						
		Recommended	C30		0.1 uF	High freqnecy noise decoupling and/or thermistor detach delay capacitor						
		Recommended	D11			Zener clamp protection for TS pin						
						Safety timer and termination setting and disable						
ттс	7	Recommended	C3 (C <sub>TTC</sub> )		*nF	Safety timer setting capacitor	Cannot be floating HIGH disables safety timer LOW disables termination and safety timer Capacitor sets safety timer duration See Electrical Characterisitics table for minimum and maximum fast charge safety timer settings					
	11					Fast charge current reference setting						
ISET1		Required	R11		*Ω	Resistor divider network for fast	$I_{CHARGE} = \frac{V_{BET 1}}{20 \dots P}$					
		Recommended	C13		*Ω 0.1 uF	High frequency noise	20 × K 38					
						Pre-charge and termination current reference setting						
			R15		*Ω	Resistor divider network for pre-						
ISET2		Required	R16		*Ω	charge and termination current setting	$I_{TERM} = \frac{V_{ISET 2}}{100 \times R_{SR}} \qquad I_{PRECLANCE} = \frac{V_{ISET 2}}{100 \times R_{SR}}$					
	15	Recommended	C18		0.1 uF	High frequency noise decoupling capacitor						
						Input current limit reference setting						
			R6		*Ω	Resistor divider network for input						
ACSET		Required	R7		*Ω	current limit setting	$20 \times R_{AC}$					
	16	Recommended	C8		0.1 uF	High frequency noise decoupling capacitor						





	COMMUNICATION AND MISC INPUT/OUTPUT SIGNAL - DESIGN CHECKLIST									
PIN NAN	ЛE	REQUIREMENT	COMPONENT	MIN	ТҮР	MAX	DESCRIPTION	COMMENTS AND RELEVANT EQUATIONS		
CE	4						Active HIGH input signal pin to enable charge	Cannot be floating HIGH enables charging LOW disables charging		
							Open-drain output signal for charging status	Refer to Datasheet Table 2 for description		
STAT1	5	Recommended	R36		10 kΩ		Charging status indicating LED			
		Optional	D5				Charging status indicating LED			
							Open-drain output signal for charging status	Refer to Datasheet Table 2 for description		
STAT2	9	Recommended	R40		10 kΩ		Charging status indicating LED			
		Optional	D6				Charging status indicating LED			
							Open-drain output signal for input power status			
/PG	8	Recommended	R35		10 kΩ		Input status indicating LED			
		Optional	D7				Input status indicating LED			
							Internal 3.3V LDO			
VREF	10	Required	C6				Internal 3.3V LDO output stabilizing capacitor			
PwrPad	-						IC Thermal dissipation pad			